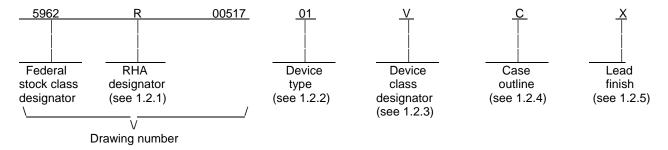
В	"V _S = +5 V Make chan																		
В	"V _S = +5 V Make chan			DESCRIPTION					DATE (YR-MO-DA)			APPROVED							
			Make change to input offset voltage tests as specified under sections; $"V_S = +5 \text{ V}, \text{ V}_{CM} = 2.5 \text{ V"} \text{ and } "V_S = +3 \text{ V}, \text{ V}_{CM} = 1.5 \text{ V"} \text{ in table I ro}$						00-11-28			R. MONNIN							
С	· ·	Make change to supply current test as specified under section; $"V_S = +3 \text{ V}, V_{CM} = 1.5 \text{ V}"$ in table I ro						00-1	12-19			R. MONNIN							
	Make change to V _{OS} delta limit as specified in TABLE IIB ro							01-10-05				R. MONNIN							
D	Add radiation	on harde	ened re	quirem	nents	ro							01-1	11-13			R. M	IONNIN	
REV SHEET																			
SHEET REV SHEET																			
SHEET REV SHEET REV STATUS			REV			D	D	D	D	D	D	D	D	D	D	D			
SHEET REV SHEET REV STATUS OF SHEETS			SHE	ET		D 1	D 2	D 3	D 4	D 5	D 6	D 7	D 8	D 9	D 10	D 11			
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A			SHE PREF Raje	ET PARED esh Pit	hadia					5	6	7 SE SI	8 UPPL	9 .Y CE	10	11 COL	_	BUS	
SHEET REV SHEET REV STATUS OF SHEETS	CIRCUIT		SHE PREF Raje	ET PARED	hadia BY					5	6	7 SE SI COL	8 UPPL UMBI	9 .Y CE US, O	10	11 R COL 43216	_	BUS	
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STANI MICROC DRAV THIS DRAWING FOR USE DEPART	CIRCUIT WING G IS AVAILA E BY ALL TMENTS	BLE	SHE PREF Raje CHEC Raje	PARED esh Pit CKED esh Pit	BY hadia	1			MIC PRI	DI DI CROC ECIS	EFEN CIRCUION,	SE SI COL http	8 UPPL UMBI o://ww	9 Y CE US, O vw.ds	NTER OHIO SCC.dl	11 R COL 43216 a.mil	6 IL-TC	D-RAI	L,
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STANI MICROC DRAV THIS DRAWING FOR USE	CIRCUIT WING G IS AVAILA E BY ALL TMENTS CIES OF TH	BLE E	SHE PREF Raje CHEC Raje APP Ray	PARELESH Pit CKED esh Pit ROVE	BY hadia D BY	1	2		MIC PRI	DI CROC	EFEN CIRCUION,	SE SI COL http	8 UPPL UMBI o://ww	9 Y CE US, O vw.ds	NTER OHIO SCC.dl	11 R COL 43216 a.mil	6 IL-TC	D-RAI	L,
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STANI MICROC DRAV THIS DRAWING FOR USE DEPART AND AGENCE	CIRCUIT WING G IS AVAILA E BY ALL TMENTS CIES OF TH F OF DEFEN	BLE E	SHE PREF Raje CHEC Raje APP Ray	PARED esh Pit CKED esh Pit ROVE mond	BY hadia D BY Monnin	0VAL D	2		MIC PRI MO	DI DI CROC ECIS	EFEN CIRCUION, ITHIC	SE SI COL http	BUPPLUMBIO://ww	9 Y CE US, O vw.ds	NTER PHIO scc.dl	11 R COL 43216 a.mil	IL-TO	D-RAI	L,

1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following example:



- 1.2.1 <u>RHA designator</u>. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	OP484A	Precision, rail-to-rail input and output,

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as follows:

Device class

Device requirements documentation

M

Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A

Q or V

Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	utline letter Descriptive designator		Package style
C	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

STANDARD						
MICROCIRCUIT DRAWING						

DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000

SIZE A		5962-00517
	REVISION LEVEL	SHEET 2

1.3 Absolute maximum ratings. 1/

Supply voltage Power dissipation Differential input voltage Input voltage Output short-circuit duration Storage temperature range Lead temperature (soldering, 60 seconds) Junction temperature (T _J) Thermal resistance, junction-to-case (θ _{JC})	500 mW ±0.6 V ±18 V Indefinite -65°C to +150°C +300°C -65°C to +150°C
Thermal resistance, junction-to-ambient (θJA): Case C	108°C/W
Supply voltage (V _S) Operating temperature range (T _A)	

1.5 Radiation features:

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- These parts may be dose rate sensitive in space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-00517
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL D	SHEET 3

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
- 3.2.3 <u>Radiation test circuit</u>. The radiation test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.
- 3.3 <u>Electrical performance characteristics and post irradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and post irradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.
- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-PRF-38535, appendix A.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M.</u> Device class M devices covered by this drawing shall be in microcircuit group number 49 (see MIL-PRF-38535, appendix A).

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-00517
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL D	SHEET 4

	T	ABLE I. <u>Electrical</u>	performance	e characteri	stics.			
Test	Symbol	$ \begin{array}{c} Conditions \\ -55^{\circ}C \leq T_{A} \leq \cdot \\ unless \ otherwise \end{array} $	+125°C	Group A		Limits		Unit
						Min	Max	
V _S = +5 V, V _{CM} = 2.5 V sec	tion							
Input offset voltage	Vos			1	01		200	μV
				2, 3			400	
		M	1,D,P,L,R	1			600	
Input offset current	Ios	<u>3</u> /		1, 2, 3	01		50	nA
		V _S = +5 V, M,D,	P,L,R	1			400	
Input bias current	IB	<u>3</u> /		1	01		350	nA
				2, 3			575	
		V _S = +5 V, M,D,	P,L,R	1			3000	_
Common-mode <u>4/</u> rejection ratio	CMRR	V _{CM} = 1.0 V to 4	.0 V	1, 2, 3	01	86		dB
Output high voltage 4/	Voн	IL = 1 mA		4	01	4.85		V
				5, 6		4.7		_
Output low voltage 4/	V _{OL}	I _L = 1 mA		4	01		125	mV
				5, 6			200	
Large signal voltage gain	A _{VO}	$R_L = 2 k\Omega$,		4	01	50		V/mV
		V _{OUT} = 1 V to 4	V	5, 6		25		
		R _L = 10 kΩ,	M,D,P,L,R	4		25		
		V _{OUT} = 1 V to 4	V					
Supply current <u>5</u> /	I _{SY}	V _{OUT} = 2.5 V		1	01		5.8	mA
		M	1,D,P,L,R	1			5.85	
V _S = +3 V, V _{CM} = 1.5 V sec	tion	- '					•	•
Input offset voltage $\frac{4}{}$	Vos			1	01		200	μV
				2, 3			400	_
Input offset current 4/	los	<u>3</u> /		1, 2, 3	01		50	nA
See footnotes at end of table	e.							
STA MICROCIRO	NDARD CUIT DRAV	VING		ZE A			596	2-00517
DEFENSE SUPPLY COLUMBUS,				F	REVISION LEVE D	EL	SHEET	5

	TABLE	Electrical performanc		i <u>cs</u> – Co	ntinued.			
Test	Symbol	Conditions $\underline{1/2}$ / $-55^{\circ}C \leq T_A \leq +125^{\circ}C$ unless otherwise speci	Gro	oup A groups	Device type	Limits		Unit
					7.	Min	Max	
V _S = +3 V, V _{CM} = 1.5 V secti	on – Continu	ued						
Input bias current 4/	I _B	<u>3</u> /		1	01		350	nA
			2	2, 3	-		575	
Common-mode <u>4</u> /	CMRR	V _{CM} = 0 V to 3 V		1	01	60		dB
rejection ratio			2	2, 3	-	56		
Output high voltage 4/	VoH	I _L = 1 mA		4	01	2.85		V
			5	i, 6	-	2.65		
Output low voltage 4/	V _{OL}	I _L = 1 mA		4	01		125	mV
			5	5, 6	-		200	
Supply current 4/5/	I _{SY}	V _{OUT} = 1.5 V		1	01		5.4	mA
$V_S = \pm 15 \text{ V}, V_{CM} = 0 \text{ V section}$	on	I			l l			
Input offset voltage 4/	Vos			1	01		250	μV
			2	2, 3			500	
Average input offset 4/	TCV _{OS}			8	01		2	μV/°C
voltage Input offset current 4/	los		1,	2, 3	01		50	nA
Input bias current 4/	I _B			1	01		350	nA
			2	2, 3	-		575	
Common-mode <u>4/</u> rejection ratio	CMRR	V _{CM} = -15 V to +15 V	1,	2, 3	01	80		dB
Power supply rejection 4/ ratio	PSRR	V _S = ±2 V to ±18 V	1,	2, 3	01	90		dB
Output high voltage 4/	VOH	I _L = 1 mA		4	01	14.8		V
			5	5, 6		14.7		
Output low voltage 4/	V _{OL}	I _L = 1 mA		4	01		-14.875	V
			5	5, 6			-14.8	_
See footnotes at end of table		ı	1					1
MICROCIRC			SIZE A				5962	2-00517
DEFENSE SUPPLY COLUMBUS, (REV	ISION LEVE D	L	SHEET	6

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	$ \begin{array}{c} Conditions \ \underline{1/\ 2/} \\ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C \\ unless \ otherwise \ specified \end{array} $	Group A subgroups	Device type	Limits		Unit
					Min	Max	
$V_S = \pm 15 \text{ V}, V_{CM} = 0 \text{ V section}$	on – Continu	ued					
Large-signal voltage 4/ gain	Avo	$R_L = 2 \text{ k}\Omega, V_{OUT} = \pm 10 \text{ V}$	4	01	150		V/mV
9			5, 6		75		_
Supply current 4/5/	I _{SY}	V _{OUT} = 0 V	1	01		8	mA
		V _S = ±18 V, V _{OUT} = 0 V	1, 2, 3			9	
Slew rate 4/	SR	$R_L = 2 k\Omega$	7	01	2.4		V/μs

- 1/ Devices supplied to this drawing have been characterized through all levels M, D, P, L, R of irradiation. However, this device is only tested at the "R" level. Pre and Post irradiation values are identical unless otherwise specified in table I. When performing post irradiation electrical measurement for any RHA level, T_A = +25°C.
- 2/ These parts may be dose rate sensitive in space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A.
- 3/ Guaranteed by $V_S = \pm 15 \text{ V test.}$
- 4/ This parameter is not tested to post irradiation.
- 5/ ISY limit equals total of all four amplifiers.

4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-00517
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL D	SHEET 7

Device type	01
Case outlines	C and D
Terminal number	Terminal symbol
1	OUTPUT A
2	-INPUTA
3	+INPUT A
4	+V _S
5	+INPUT B
6	-INPUT B
7	OUTPUT B
8	OUTPUT C
9	-INPUT C
10	+INPUT C
11	-Vs
12	+INPUT D
13	-INPUT D
14	OUTPUT D

FIGURE 1. <u>Terminal connections</u>.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE A		5962-00517
		REVISION LEVEL D	SHEET 8

- 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- 4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
 - 4.4.1 Group A inspection.
 - a. Tests shall be as specified in table IIA herein.
 - b. Subgroups 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.
 - 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.
 - 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - b. $T_A = +125^{\circ}C$, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000	SIZE A		5962-00517
		REVISION LEVEL D	SHEET 9

TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	(in accord	roups lance with 535, table III)
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1,2,3,4,5,6,7,8 <u>1</u> /	1,2,3,4,5,6, <u>1</u> / 7,8	1,2,3,4, <u>1</u> / <u>2</u> / 5,6,7,8
Group A test requirements (see 4.4)	1,2,3,4,5,6,7,8	1,2,3,4,5,6, 7,8	1,2,3,4,5,6, 7,8
Group C end-point electrical parameters (see 4.4)	1	1	1 <u>2</u> /
Group D end-point electrical parameters (see 4.4)	1	1	1
Group E end-point electrical parameters (see 4.4)	1,4	1,4	1,4

- 1/ PDA applies to subgroup 1. V_{OS} excluded from PDA.
 2/ Delta limits as specified in table IIB shall be required where specified, and delta limits shall be computed with reference to the previous endpoint electrical parameters.

TABLE IIB. 240 hour burn-in and group C end-point electrical parameters. T_A = 25°C

Parameter	Device type	Limit	Delta <u>1</u> /
Vos	01	±250 μV	±250 μV
I _{IB}		350 nA	100 nA
los		50 nA	40 nA

- $\underline{1}$ / Delta limits apply to ± 15 V operation.
- 4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes M, Q, and V shall be as specified in MIL-PRF-38535. End point electrical parameters shall be as specified in table IIA herein.
- 4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A, and as specified herein

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-00517
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL D	SHEET 10

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.
 - 6.1.2 Substitutability. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA , Columbus, Ohio 43216-5000, or telephone (614) 692-0547.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.
 - 6.6 Sources of supply.
- 6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.
- 6.6.2 <u>Approved sources of supply for device class M.</u> Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD			
MICROCIRCUIT DRAWING			
DEFENSE SUPPLY CENTER COLUMBUS			

COLUMBUS, OHIO 43216-5000

SUS

SIZE **5962-00517**REVISION LEVEL SHEET **D** 11

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 01-11-13

Approved sources of supply for SMD 5962-00517 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-0051701VCA	24355	OP484AY/QMLV
5962-0051701VDA	24355	OP484AM/QMLV
5962R0051701VCA	24355	OP484AY/QMLR
5962R0051701VDA	24355	OP484AM/QMLR

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number

Vendor name and address

24355 **Analog Devices** RT 1 Industrial Park PO Box 9106 Norwood, MA 02062

Point of contact: 1500 Space Park Drive

PO Box 58020

Santa Clara, CA 95052-8020

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.